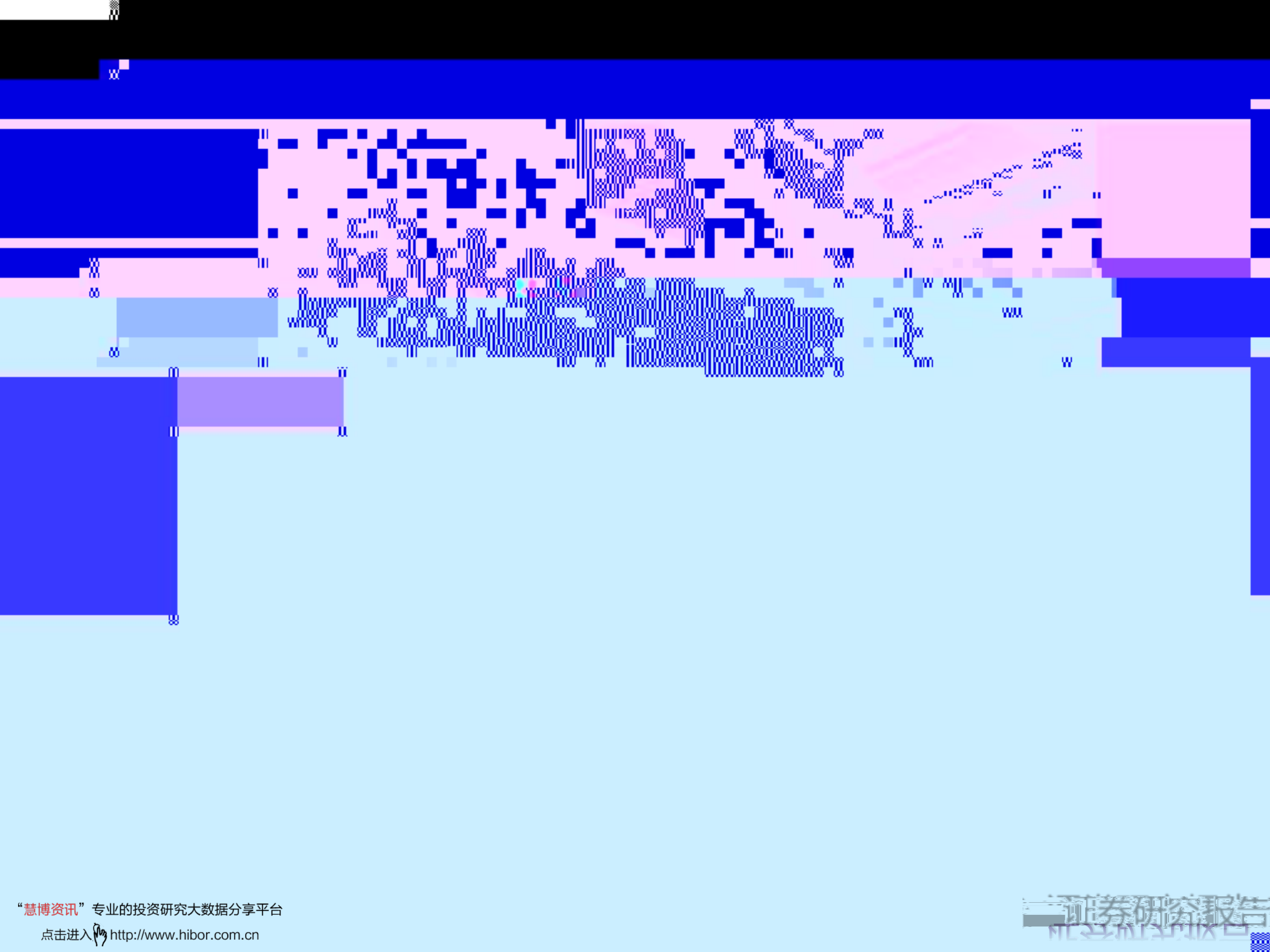




1

2

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5

1

IDM

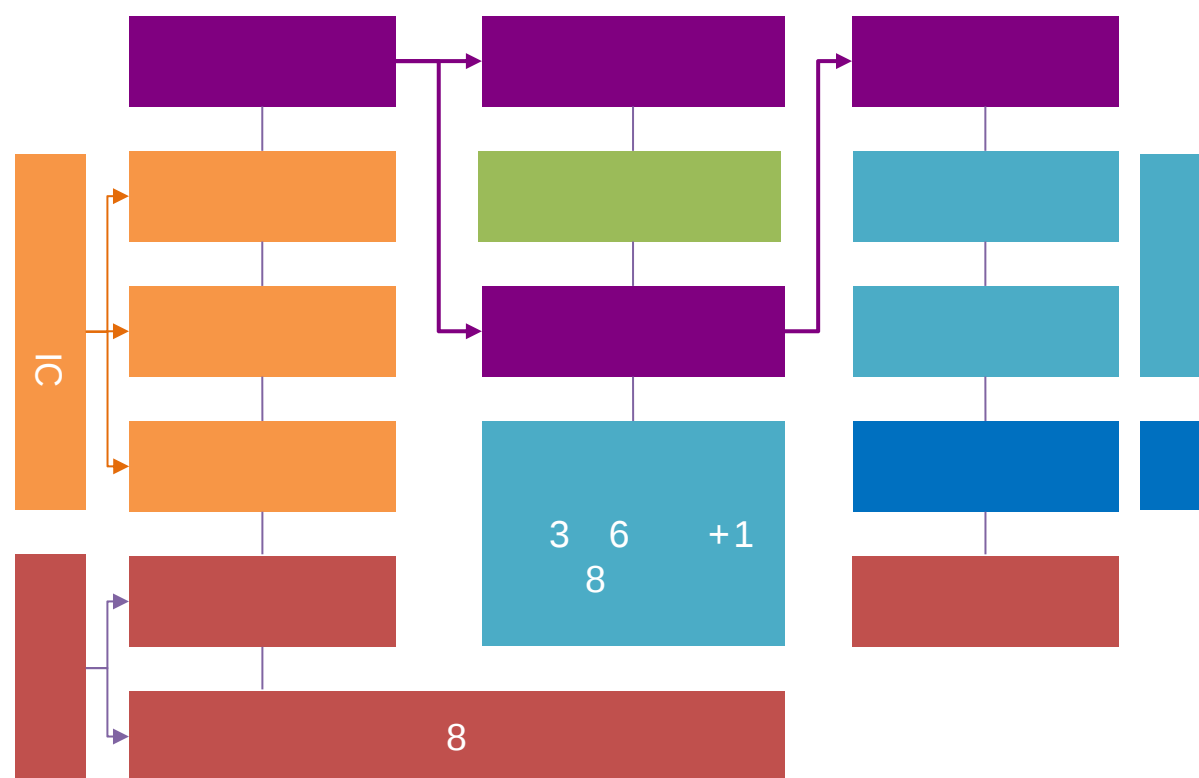
IDM

IDM

IDM

1983	•	4
1988	•	
1999	•	6 MOS
2000	•	
2003	•	
2007	•	8
2008	•	(0597.HK)
2009	•	8
2011	•	
2013	•	8 4
2014	•	
2016	•	8 6
2017	•	52.41%
2018	•	0.18 BCD
2020	•	

IDM

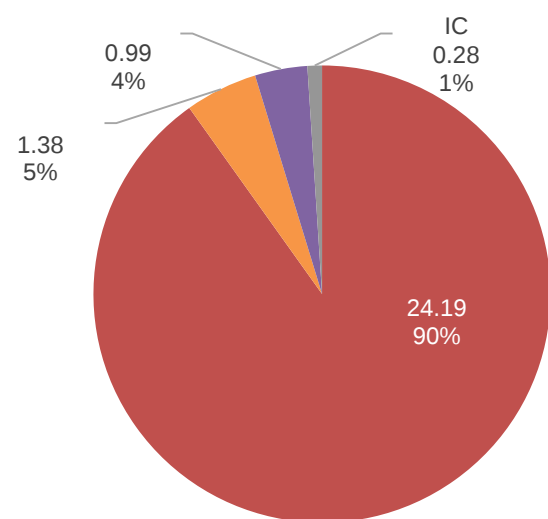


			2018
	3 6	Analog BCD MEMS DMOS Power Discrete	247
	1 8	Advance BCD Analog DMOS	

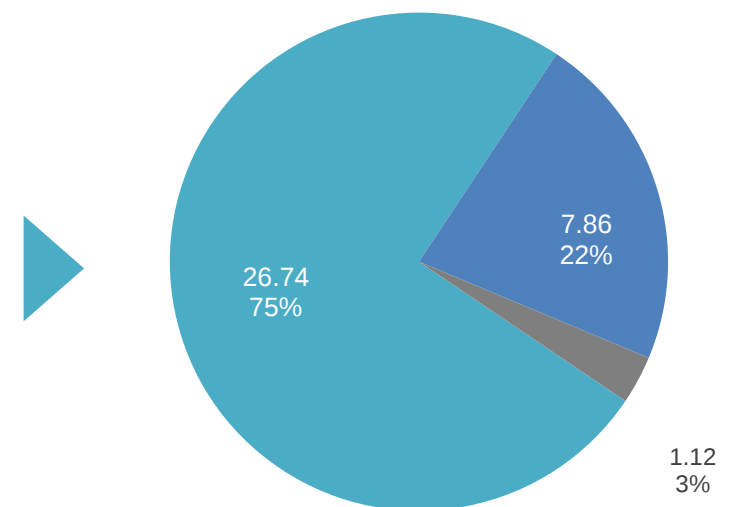
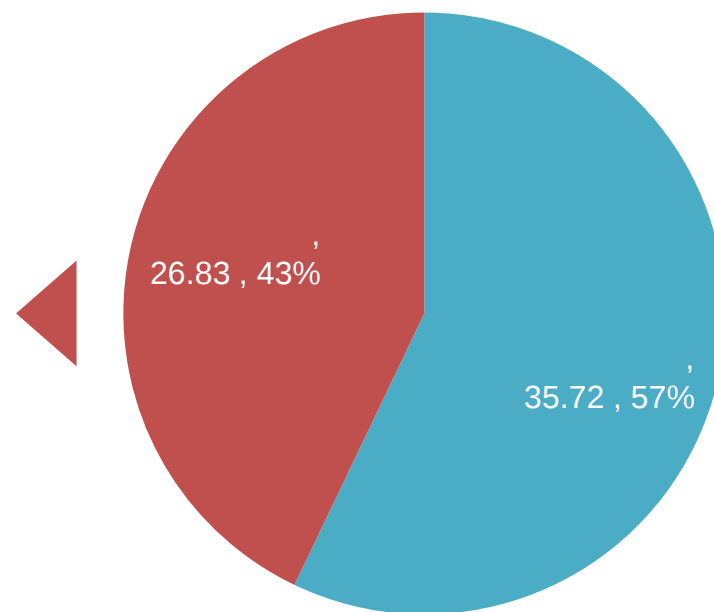
IDM

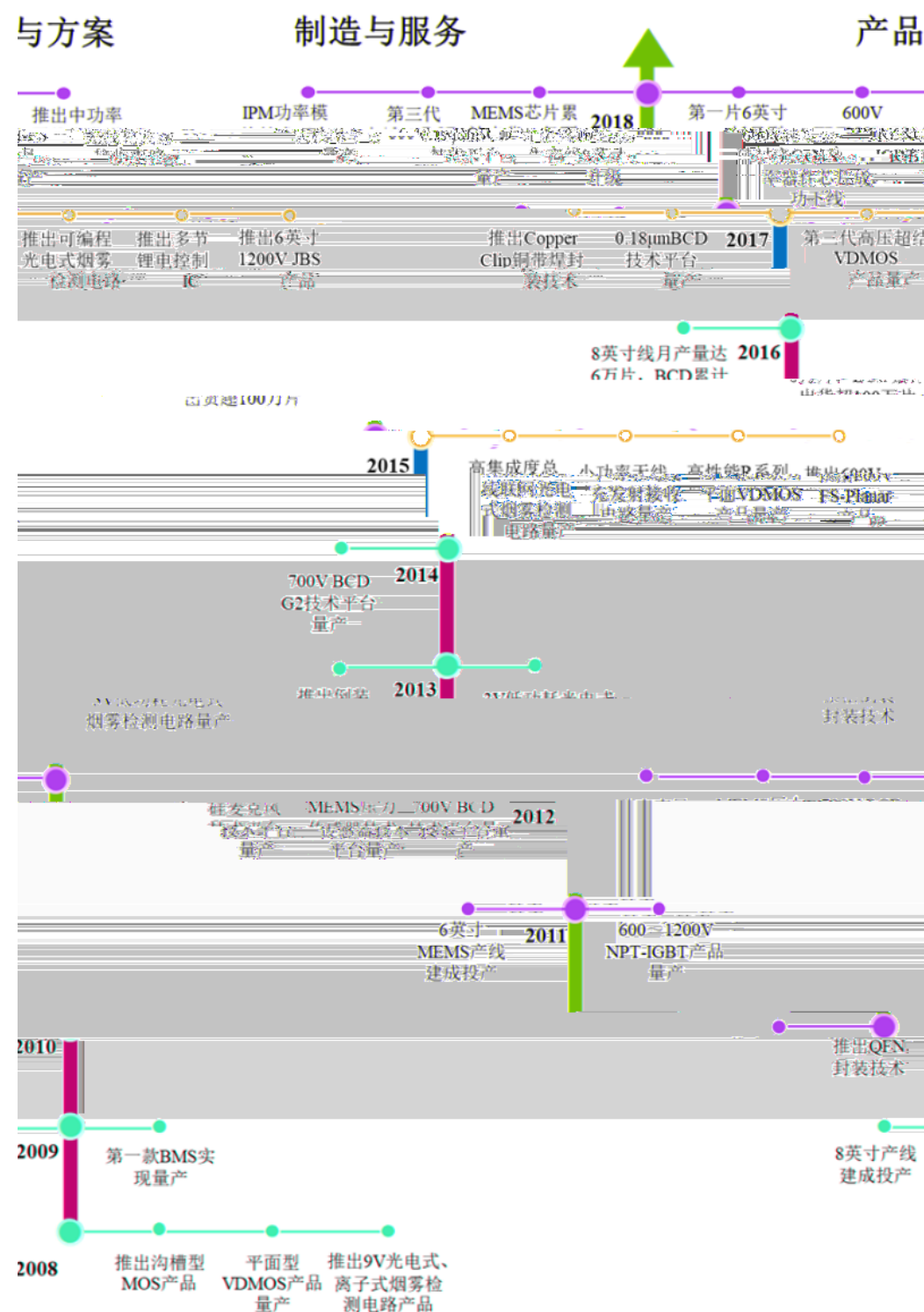
IDM
TCL MPS

2018



wind





1 IDM

MOSFET

IGBT SBD FRD

		h	

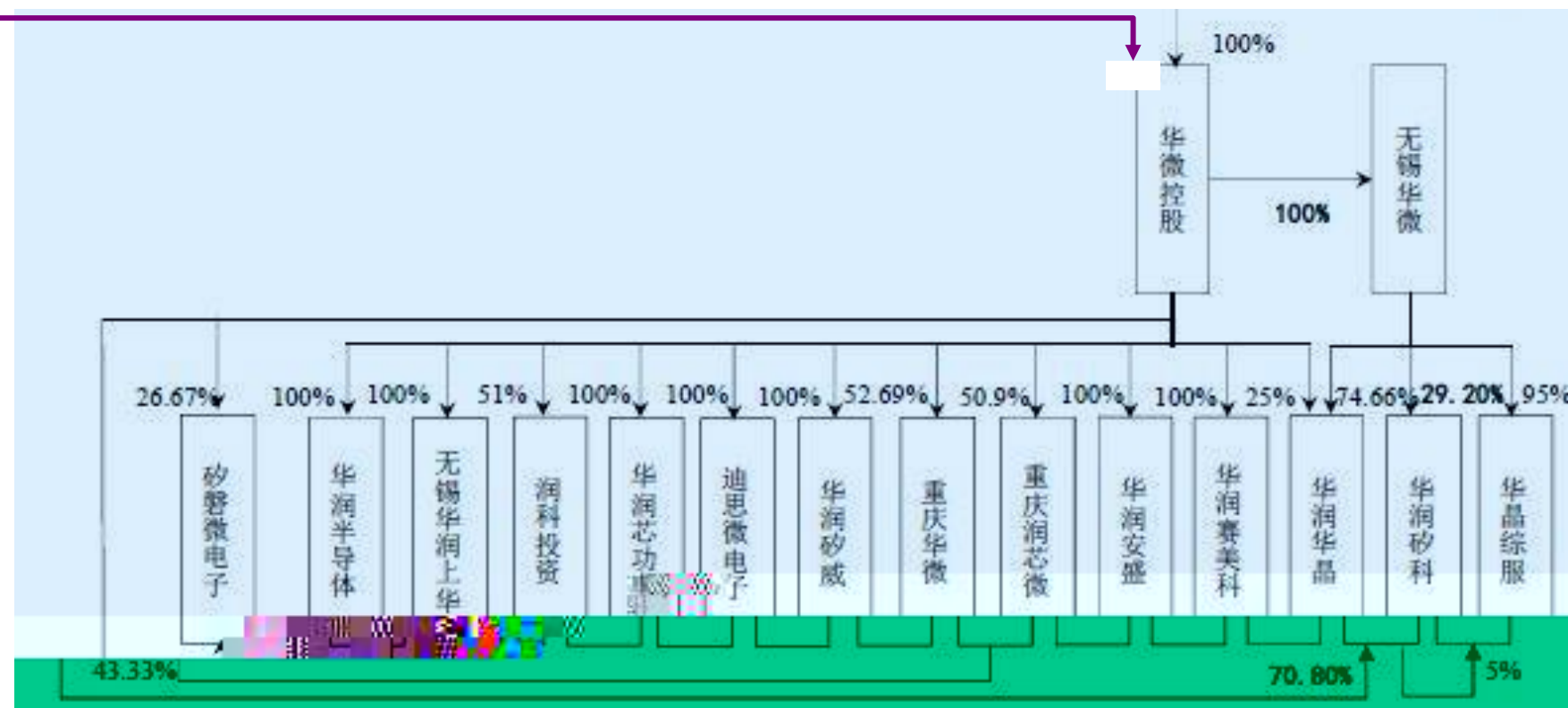
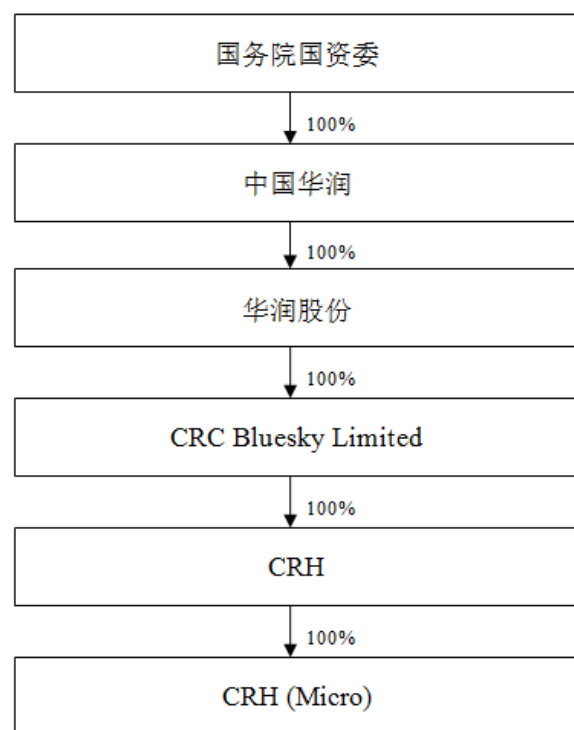
2

	1	8		3	6			1.0-0.11μm	
				SOI	BCD		CMOS	CMOS	Bipolar BiCMOS
IGBT				GaN	SiC				
	1	8							IC

			2018
	3 6	Analog BCD MEMS DMOS Power Discrete	247
	1 8	Advance BCD Analog DMOS	73
	1 8	MOS MOS MOS MOS SBD	60
			199
		QFP QFN PQFN FC-QFN TSSOP SSOP MSOP IPM	62
			69
			2.4

100%

202001



2

2019Q1-3	41.32	2.70
2019Q1-3	22.38%	8.58%
	4.50	36.93%

2019Q1-3

41.32

2.70

2017

2018

14.73%

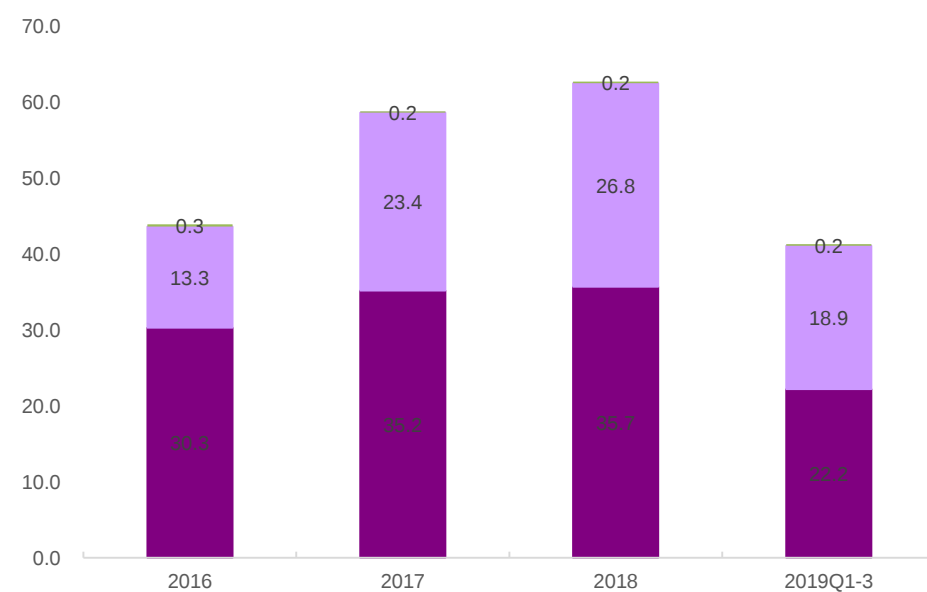
1.48%

2019H1

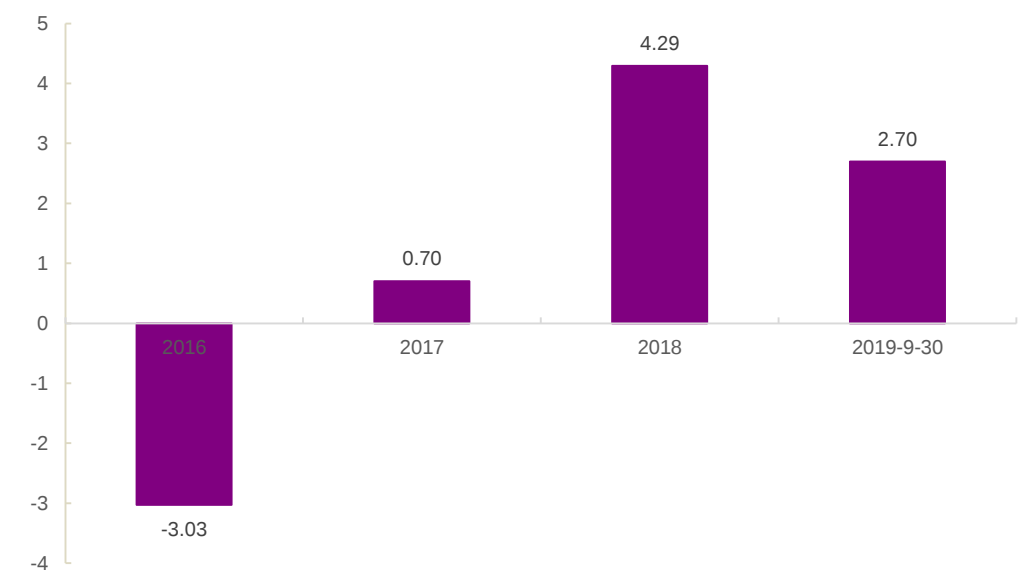
2019Q1-3

41.32

2.70



wind



wind

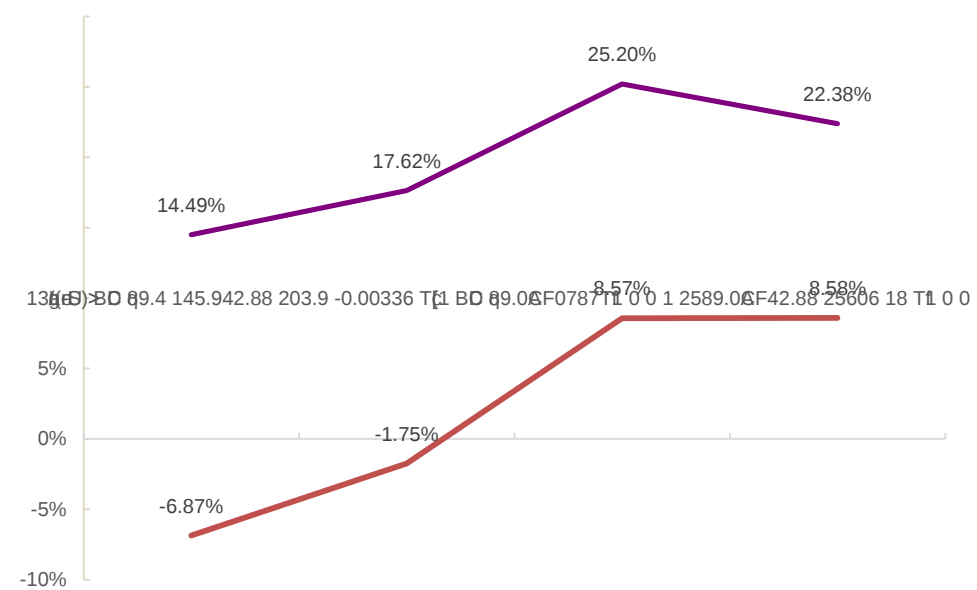
2019Q1-3

22.38%

8.58%

2018
2018

2017
2017 3.49



wind

wind

		2018	2017
	8	184,311.28	180,873.09
	8	397,317.05	387,233.01
	6	149,987.39	150,333.55
	6 1	84,667.33	78,746.57
	6 2	52,562.94	58,083.76
		45,152.93	45,346.07
		119,878.92	111,623.56
		23,639.78	21,216.57
		17,854.81	17,172.57
	8	24.91%	31.23%
	8	19.94%	25.09%
	6	15.52%	15.73%
	6 1	27.25%	27.21%
	6 2	9.61%	12.89%
		23.56%	25.31%
		36.81%	38.12%
		42.09%	44.36%
		33.60%	38.33%
	8	13,409.48	38,832.46
	8	27,620.75	38,700.45
	6	2,957.87	3,549.41
	6 1	4,468.50	4,501.33
	6 2	1,215.46	1,972.54
		2,530.98	2,455.20
		7,873.66	7,103.02
		1,873.14	1,738.79
		1,264.87	1,467.87
		63,214.71	100,321.07

2018		2017
	2018	
2017	37,106.36	
2018		25,422.98
	8	
2017		2018
	11,079.70	
2018		2017
2017		



4.50

36.93%

2018

4.50

7.17%

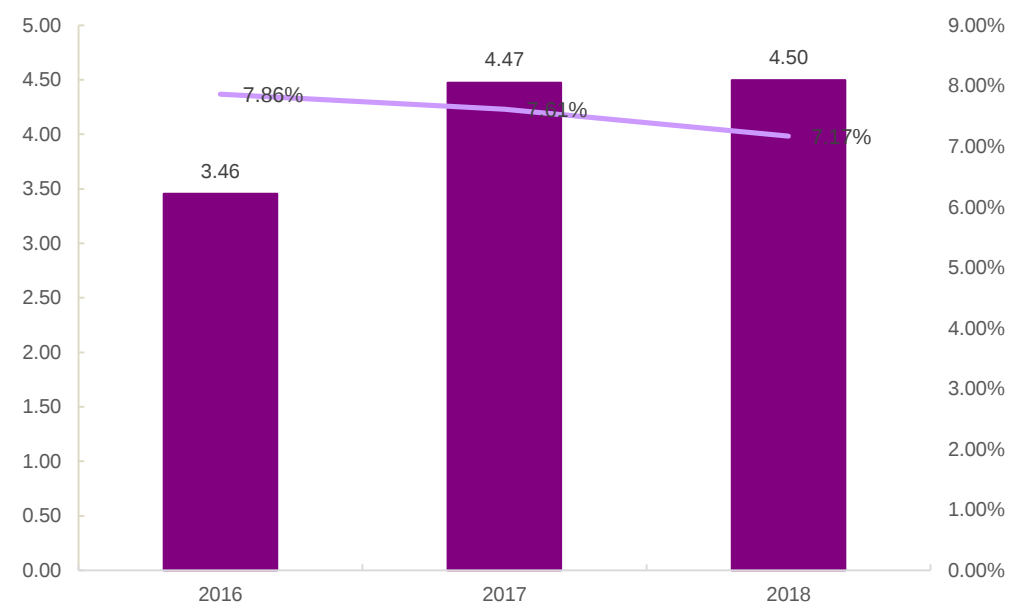
2019 6 30

7,937

641

2,290

36.93%



wind

	641	2290
		IC
		IC
	“ ”	“ ” “ ”

	2019	2018	2017	2016
	10,637.48	24,362.19	21,114.47	15,596.51
	879	872	796	691
	12.10	27.94	26.53	22.57

2018

80%

20%

IDM

2018

78%

5

2019	1		5,195.50	4.56%
	2		4,738.29	4.16%
	3		3,891.76	3.41%
	4		3,767.30	3.30%
	5		3,696.06	3.24%
			21,288.91	18.67%

wind

2019

2019	1		7,889.40	5.31%
	2	MPS International, Ltd	7,222.97	4.86%
	3		5,149.24	3.46%
	4		5,114.96	3.44%
	5	Diodes Incorporated	4,864.30	3.27%
			30,240.87	20.34%

wind

1

2

3

4

5

3

MOEFET

$$\begin{array}{ccccccc} & & = & & + & & \text{IC} \\ 2020 & & 422 & & & & 153 & & 4\% \\ & & & & \text{MOEFET} & & & & \\ & & \text{IDM} & & & & & & \end{array}$$



= + IC

IC

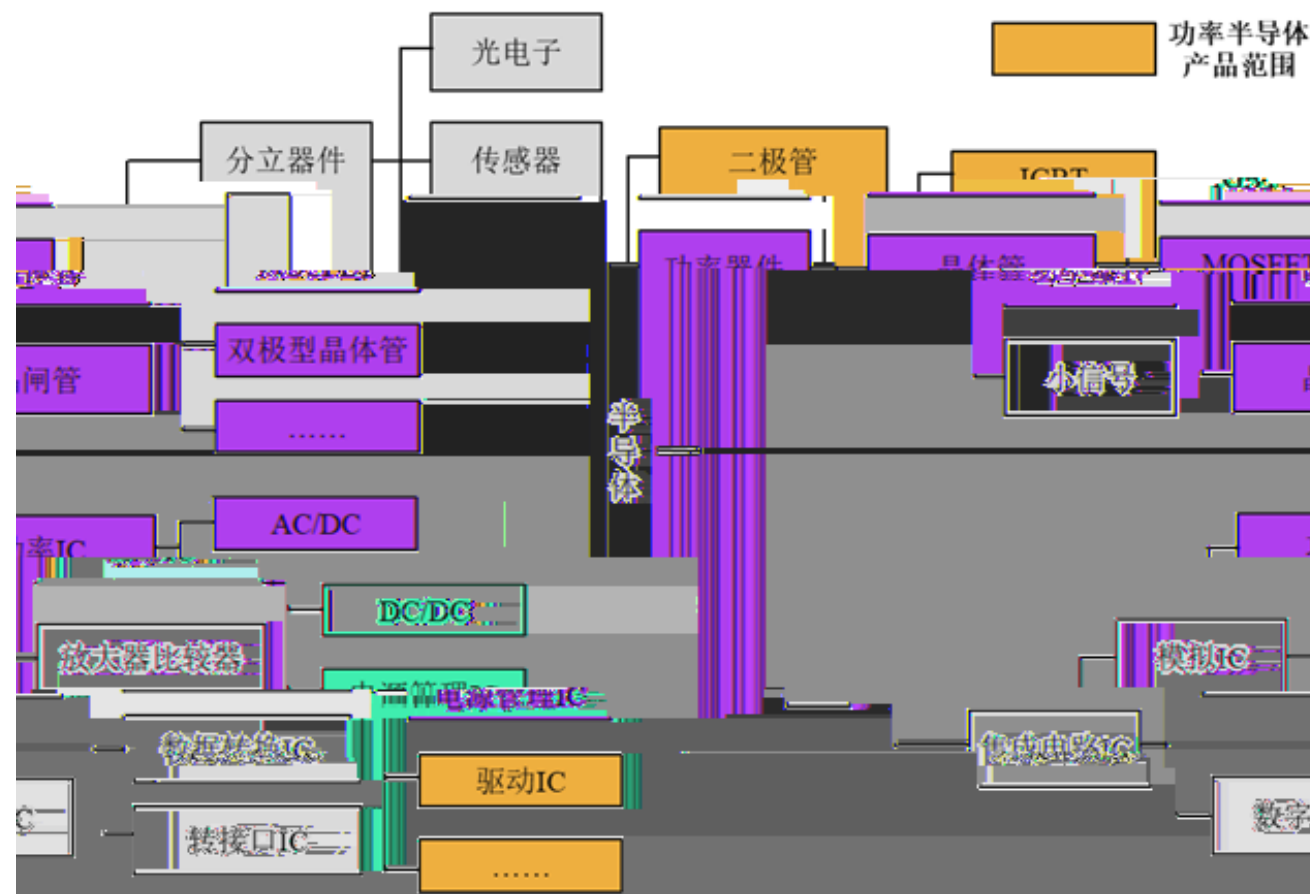
IHS Markit

MOSFET

IGBT

5

= + IC



2020

422

153

4%

IHS Markit

2018

391

2021

441

4.1%

2018

138

9.5%

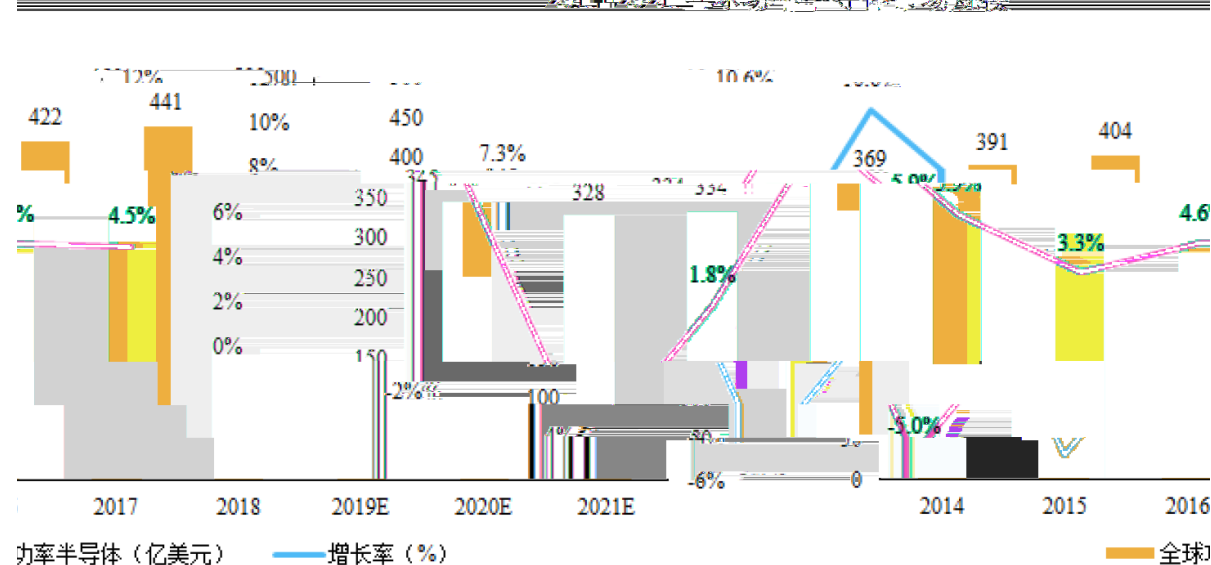
35%

2021

159

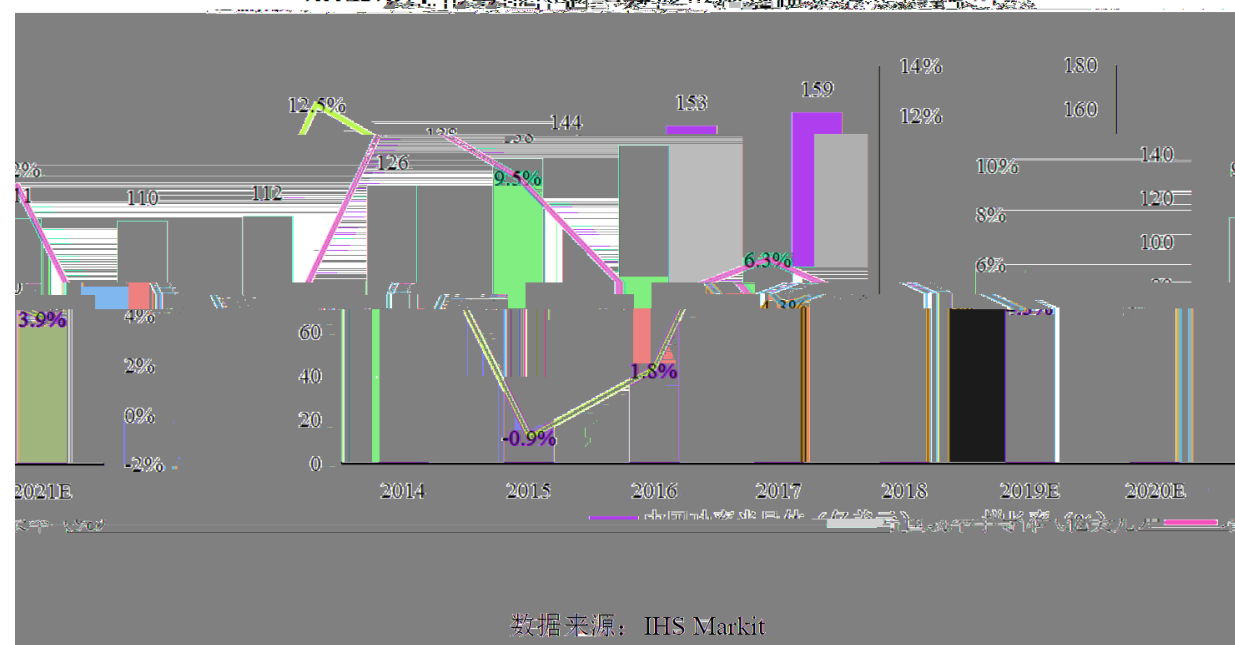
4.8%

2014-2021 全球功率半导体市场规模



数据来源: IHS Markit

2014-2021 年中国功率半导体市场规模及增长预测



数据来源: IHS Markit



光大电子
杨明辉 186-8946-4694
耿 正 136-7166-5736

光大电子
杨明辉 186-8946-4694
耿 正 136-7166-5736

光大电子

MOEFET



2018

		2018 MOSFET	
1		52	28.4%
2		31	16.9%
3		16	8.7%
4		12	6.6%
5		12	6.6%
6		9	4.9%
7		51	27.9%
		183	100%

IHS Markit

IDM

2018

10

10

IDM

2018

2018

		2018	
1		509	
2		248	
3		239	
4		225	
5		111	
6	()	107	
7		92	
8		66	
9		65	
10		63	IDM

2018

		2018
1		21.7
2		18.5
3		17.1
4		8.1
5		7.7
6		7.2
7		6.9
8		6.0
9		5.4
10		4.9



IDM

2018

IDM

IDM

1,100
MEMS

500 IC
IPM

BCD

2019 6 30

1,173

2,428
152

282

1,325

“ ”

1

2

3

4

5



8

8

8 BCD

BCD MEMS 8 MEMS 16,000

IC MEMS

50% 20% 30%

1	8	15	50%
2		6	20%
3		3	10%
4		6	20%
		30	100%

1

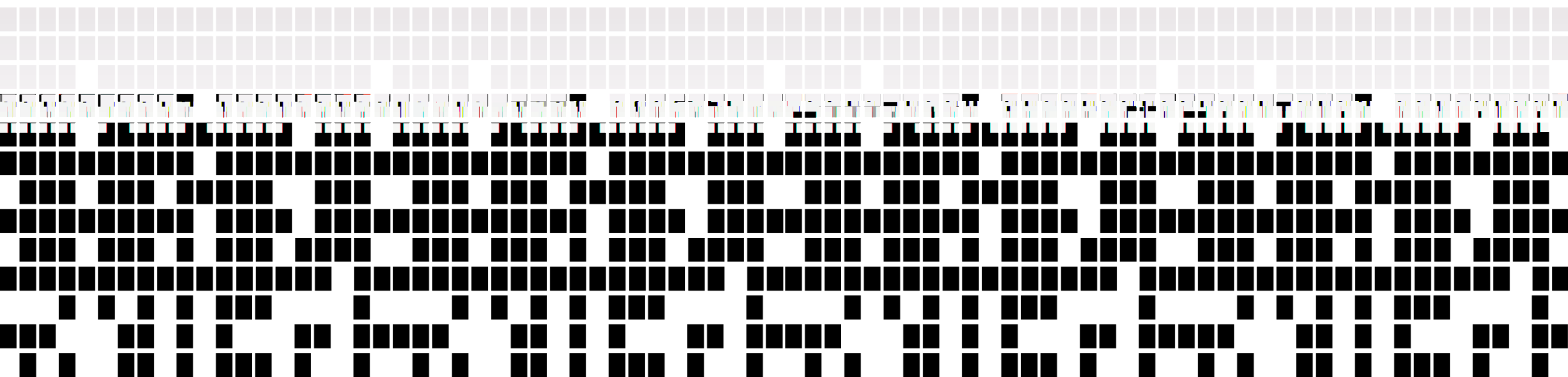
2

3

4

5





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THANKYOU!



CREATIVE

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—	6-12	15%	
—	6-12	5%	15%
—	6-12		-5% 5%
—	6-12	5%	15%
—	6-12	15%	

A 300

“ ” 1996

“ ”